



# 7th RD50 Workshop

## Monday 14 November 2005

### Pad Detector Characterization (PDC) - 40-S2-A01 (09:15 - 13:30)

time	[id] title	presenter
09:15	[7] A simple model for the equivalent circuit of heavily irradiated Si diodes in standard CV measurements	ALEXANDRE CHILINGAROV
09:35	[4] Comparison of full depletion voltage values extracted from C-V, I-V characteristics and charge collection measurements for a highly irradiated epi-detector	ECKHART FRETWURST
09:55	[1] Radiation Tolerance of EPI-Detectors - Recent results and future plans	GUNNAR LINDSTROEM
10:15	[8] Room temperature annealing of epi-Si detectors	IRENA DOLENC
10:35	[6] Coffee Break	
11:05	[3] Radiation hardness of pad detectors manufactured on different silicon substrates	VLADIMIR KHOMENKOV
11:25	[5] Discussion: Pad Detector Characterization	GREGOR KRAMBERGER AND ECKHART FRETWURST
11:55	[2] Lunch Break	